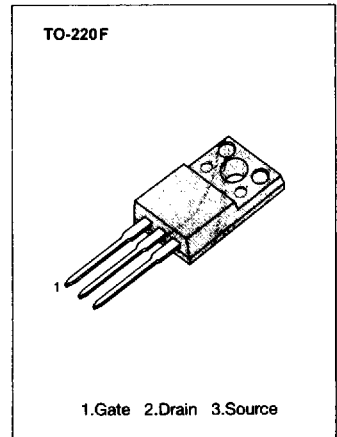


## FEATURES

- Lower  $R_{DS(ON)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

## PRODUCT SUMMARY

Part Number	V <sub>DS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
SSS6N60	600V	1.8 $\Omega$	3.2A
SS64N55	550V	1.8 $\Omega$	3.2A



## ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	SSS6N60	SSS6N55	Unit
Drain-Source Voltage (1)	V <sub>DSS</sub>	600	550	V <sub>dc</sub>
Drain-Gate Voltage (R <sub>GS</sub> =1.0M $\Omega$ )(1)	V <sub>DGR</sub>	600	550	V <sub>dc</sub>
Gate-Source Voltage	V <sub>GS</sub>	$\pm 20$		V <sub>dc</sub>
Continuous Drain Current T <sub>c</sub> =25 °C	I <sub>D</sub>	3.2		A <sub>dc</sub>
Continuous Drain Current T <sub>c</sub> =100 °C	I <sub>D</sub>	2.3		A <sub>dc</sub>
Drain Current - Pulsed (3)	I <sub>DM</sub>	24		A <sub>dc</sub>
Gate Current - Pulsed	I <sub>GM</sub>	$\pm 1.5$		A <sub>dc</sub>
Single Pulsed Avalanche Energy (4)	E <sub>AS</sub>	183		mJ
Avalanche Current	I <sub>AS</sub>	3.4		A
Total Power Dissipation at T <sub>c</sub> =25 °C	P <sub>D</sub>	40		Watts
Derate above 25 °C		0.32		W/ °C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150		°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T <sub>L</sub>	300		°C

Notes : (1) T<sub>J</sub>=25°C to 150°C

(2) Pulse test : Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$

(3) Repetitive rating ; Pulse width limited by max. junction temperature

(4) L=27mH, V<sub>GS</sub>=50V, R<sub>G</sub>=25  $\Omega$  , Starting T<sub>J</sub>=25°C

**ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage					
	SSS6N60	600	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
	SSS6N55	550	-	-	V	
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	-	4.5	nA	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
I <sub>GSS</sub>	Gate-Source Leakage Forward	-	-	100	nA	V <sub>GS</sub> =20V
I <sub>GSS</sub>	Gate-Source Leakage Reverse	-	-	-100	μA	V <sub>GS</sub> =-20V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	-	-	250	μA	V <sub>DS</sub> =Max. Rating, V <sub>GS</sub> =0V
		-	-	1000	A	V <sub>DS</sub> =0.8 Max. Rating, V <sub>GS</sub> =0V, T <sub>C</sub> =125°C
R <sub>DS(on)</sub>	Static Drain-Source On	-	-	1.8	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =3A
	Resistance(2)			1.2	Ω	
g <sub>fs</sub>	Forward Transconductance (2)	3.0	4.8	1800	Ω	V <sub>DS</sub> ≥ 50V, I <sub>D</sub> =3A
C <sub>iss</sub>	Input Capacitance	-	-	350	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz
C <sub>oss</sub>	Output Capacitance	-	-	150	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	-	-	60	pF	
t <sub>d(on)</sub>	Turn-On Delay Time	-	-	150	ns	V <sub>DD</sub> =0.5 BV <sub>DSS</sub> , I <sub>D</sub> =6A, Z <sub>θ</sub> =9.1Ω (MOSFET switching times are essentially independent of operating temperature)
t <sub>r</sub>	Rise Time	-	-	200	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	-	-	120	ns	
t <sub>f</sub>	Fall Time	-	-	77	ns	
Q <sub>g</sub>	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	-	nC	
Q <sub>gs</sub>	Gate-Source Charge	-	9.3	-	nC	
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	-	29.3	-	nC	

**THERMAL RESISTANCE**

Symbol	Characteristics		All	Units	Remark
R <sub>thJC</sub>	Junction-to-Case	MAX	3.12	K/W	
R <sub>thCS</sub>	Case-to-Sink	TYP	0.5	K/W	Mounting surface flat, smooth and greased
R <sub>thJA</sub>	Junction-to-Ambient	MAX	62.5	K/W	Free Air Operation

Notes : (1) T<sub>J</sub>=25°C to 150°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

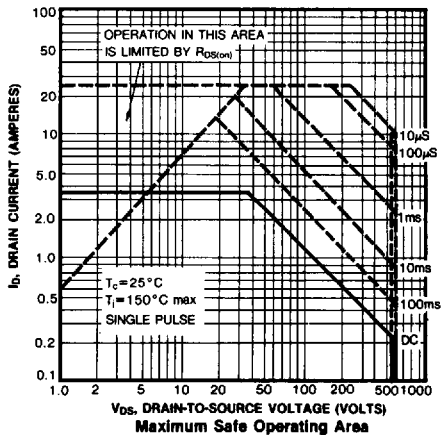
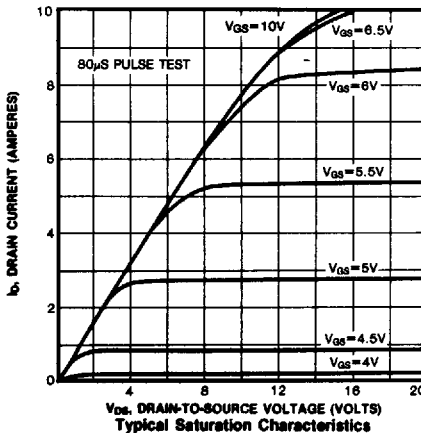
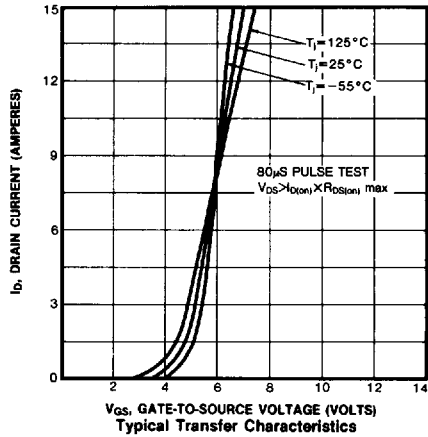
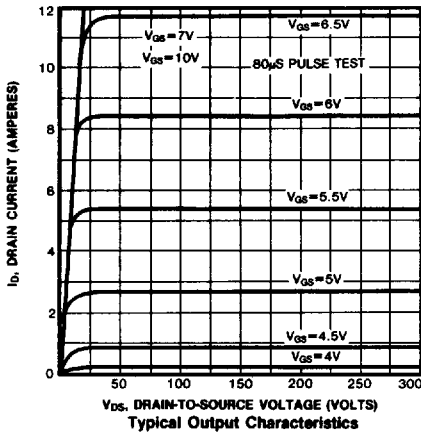


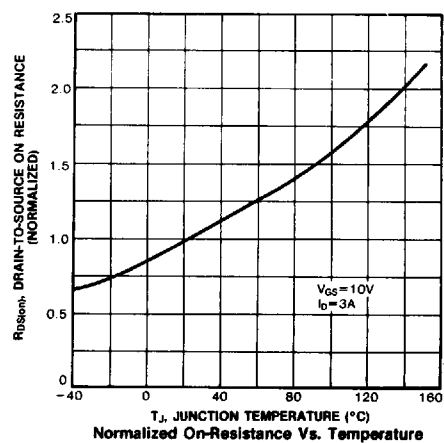
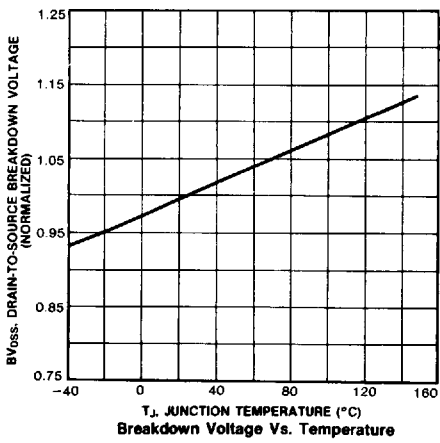
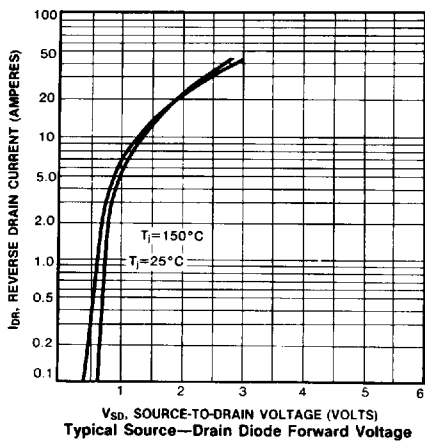
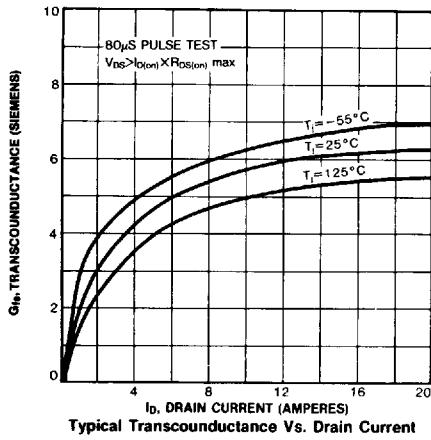
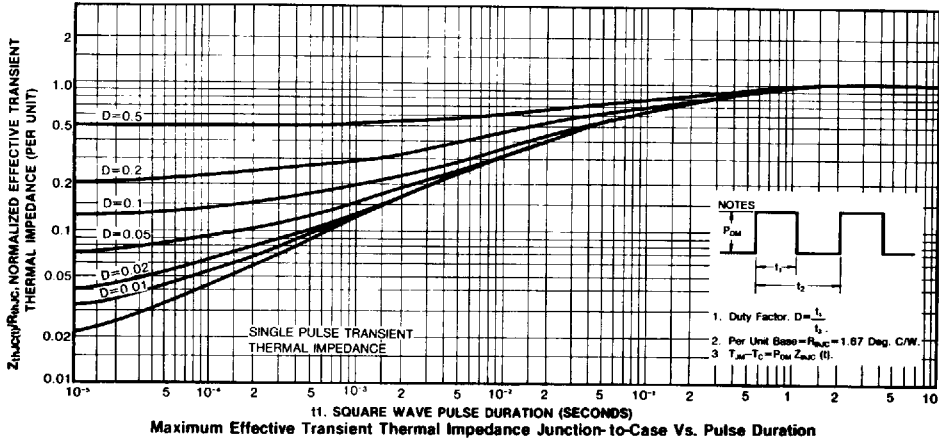
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	-	-	6	A	Modified MOSFET Symbol showing the integral reverse P-N junction rectifier
$I_{SM}$	Pulse Source Current (Body Diode) (3)	-	-	24	A	
$V_{SD}$	Diode Forward Voltage (2)	-	-	1.5	V	$T_J=25^\circ\text{C}$ , $I_S=6\text{A}$ , $V_{GS}=0\text{V}$
$t_r$	Reverse Recovery Time	-	450	940	ns	$T_J=25^\circ\text{C}$ , $I_F=6\text{A}$ , $dI_F/dt=100\text{A}/\mu\text{S}$



- Notes: (1)  $T_J=25^\circ\text{C}$  to  $150^\circ\text{C}$   
 (2) Pulse test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$   
 (3) Repetitive rating: Pulse with limited by max. junction temperature





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